

## IN THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Cancelled)

2. (Currently Amended) The method of claim ~~[[1]]~~1, wherein the forming a trench includes forming a trench which is ~~[[the]]~~a type having a (SAS) self-aligned source.

3. (Currently Amended) The method of claim ~~[[1]]~~1, wherein the forming a trench includes forming a trench so as to result in the protective resin formed from a thick (DUV) Deep Ultraviolet resin.

4. (Currently Amended) The method of claim ~~[[2]]~~2, wherein the forming a trench includes forming a trench so as to result in the protective resin formed from a thick (DUV) Deep Ultraviolet resin.

5. (Cancelled)

6. (Cancelled)

7. (Currently Amended) ~~[[The]]~~A method of claim 5, for producing a flash memory comprising:

forming at least two adjacent rows of precursor stacks of floating gate transistors on a semiconductor substrate, with the precursor stacks being at least partially covered by a protective resin and being separated by a formation zone for a source line, wherein the forming at least two adjacent rows of precursor stacks of floating gate transistors on a semiconductor substrate includes forming a semiconductor substrate with a drain for each precursor stack,

wherein the drain is covered in a resin; and

wherein for each of the precursor stacks, the drain is formed opposite the

formation zone for the source line;

forming a trench in the formation zone for the source line by an attack of the formation zone and of the protective resin so as to result in a deposit of residue from the protective resin below the precursor stacks, wherein the forming a trench includes forming a trench so as to result in the protective resin formed of thick i-line resin;

removing the deposit of residue; and

implanting a source line in the formation zone, with at least a portion of the source line extending directly below the precursor stacks.

8. (Currently Amended) [[The]]A method of claim 5, for producing a flash memory comprising:

forming at least two adjacent rows of precursor stacks of floating gate transistors on a semiconductor substrate, with the precursor stacks being at least partially covered by a protective resin and being separated by a formation zone for a source line, wherein the forming at least two adjacent rows of precursor stacks of floating gate transistors on a semiconductor substrate includes forming a semiconductor substrate with a drain for each precursor stack,

wherein the drain is covered in a resin; and

wherein for each of the precursor stacks, the drain is formed opposite the formation zone for the source line;

forming a trench in the formation zone for the source line by an attack of the formation zone and of the protective resin so as to result in a deposit of residue from the protective resin below the precursor stacks, wherein the forming a trench includes forming a trench which is [[the]]a type having a (SAS) self-aligned source;

removing the deposit of residue; and

implanting a source line in the formation zone, with at least a portion of the source line extending directly below the precursor stacks.

9. (Currently Amended) The method of claim [[1]]7, wherein the removing the deposit of residue includes removing the deposit of residue by generating dioxygen plasma.

10. (Original) The method of claim 4, wherein the removing the deposit of residue includes removing the deposit of residue by generating dioxygen plasma.

11. (Currently Amended) The method of claim [[6]]2, wherein the removing the deposit of residue includes removing the deposit of residue by generating dioxygen plasma.

12. (Original) The method of claim 8, wherein the removing the deposit of residue includes removing the deposit of residue by generating dioxygen plasma.

13. (Currently Amended) The method of claim [[1]]Z, further comprising:  
removing the protective resin following implantation of the source line.

14. (Currently Amended) The method of claim [[4]]2, further comprising:  
removing the protective resin following implantation of the source line.

15. (Currently Amended) The method of claim [[6]]4, further comprising:  
removing the protective resin following implantation of the source line.

16. (Original) The method of claim 8, further comprising:  
removing the protective resin following implantation of the source line.

17. (Original) The method of claim 12, further comprising:  
removing the protective resin following implantation of the source line.

18. (Currently Amended) The method of claim [[1]]Z, wherein the implanting the source line includes doping the source line with arsenic.

19. (Currently Amended) The method of claim [[1]]Z, wherein the Implanting the source line includes implanting the source line 25 nanometers out from an edge under a gate oxide of the precursor stacks.

20. (Cancelled).